Roberta Nipoti

List of Publications by Year
in descending order

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212	2,072	22	34
papers	citations	h-index	g-index
		304602	377752

214	214	214	1129
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	OCVD Measurement of Ambipolar and Minority Carrier Lifetime in 4H-SiC Devices: Relevance of the Measurement Setup. IEEE Transactions on Electron Devices, 2021, 68, 3254-3260.	1.6	3
2	4Hâ€SiC surface morphology after Al ion implantation and annealing with Câ€cap. Journal of Microscopy, 2020, 280, 229-240.	0.8	7
3	The Role of Defects on Forward Current in 4H-SiC p-i-n Diodes. IEEE Transactions on Electron Devices, 2019, 66, 3028-3033.	1.6	10
4	<i>(Invited)</i> Al⁺ Ion Implanted 4H-SiC: Electrical Activation versus Annealing Time. ECS Transactions, 2019, 92, 91-98.	0.3	4
5	1300Â°C Annealing of 1 Ã— 10²⁰Âcm^{âˆ’3} Al⁺ Ion Implanted 3C-SiC/Si. ECS Journal of Solid State Science and Technology, 2019, 8, P480-P487.	0.9	4
6	Activation Energy for the Post Implantation Annealing of 10¹⁹ cm⁻³ and 10²⁰cm⁻³ Ion Implanted Al in 4H SiC. Materials Science Forum, 2019, 963, 416-419.	0.3	3
7	Carrier Transport Mechanisms in Ion Implanted and Highly-Doped p-Type 4H-SiC(Al). Materials Science Forum, 2019, 963, 318-323.	0.3	2
8	(Invited) Al+ Ion Implanted 4H-SiC: Electrical Activation versus Annealing Time. ECS Meeting Abstracts, 2019, , .	0.0	0
9	Perimeter and Area Components in the ${I}$ â€" ${V}$ Curves of 4H-SiC Vertical p+-i-n Diode With Al+ Ion-Implanted Emitters. IEEE Transactions on Electron Devices, 2018, 65, 629-635.	1.6	6
10	Defects related to electrical doping of 4H-SiC by ion implantation. Materials Science in Semiconductor Processing, 2018, 78, 13-21.	1.9	20
11	(Invited) Controlling the Carbon Vacancy in 4H-SiC by Thermal Processing. ECS Transactions, 2018, 86, 91-97.	0.3	2
12	Ni-Al-Ti Ohmic Contacts with Preserved Form Factor and Few 10⁻ ⁴ Î©cm² Specific Resistance on 0.1-1 Î©cm p-Type 4H-SiC. Materials Science Forum, 2018, 924, 385-388.	0.3	4
13	Kinetics Modeling of the Carbon Vacancy Thermal Equilibration in 4H-SiC. Materials Science Forum, 2018, 924, 233-236.	0.3	1
14	3C-SiÐ¡ Hetero-Epitaxially Grown on Silicon Compliance Substrates and New 3C-SiÐ¡ Substrates for Sustainable Wide-Band-Gap Power Devices (CHALLENGE). Materials Science Forum, 2018, 924, 913-918.	0.3	12
15	(Invited) Controlling the Carbon Vacancy in 4H-SiC By Thermal Processing. ECS Meeting Abstracts, 2018, , .	0.0	0
16	Al⁺ Ion Implanted 4H-SiC Vertical p⁺-i-n Diodes: Processing Dependence of Leakage Currents and OCVD Carrier Lifetimes. Materials Science Forum, 2017, 897, 439-442.	0.3	5
17	Thermodynamic equilibration of the carbon vacancy in 4H-SiC: A lifetime limiting defect. Journal of Applied Physics, 2017, 122, .	1.1	20
18	OCVD Lifetime Measurements on 4H-SiC Bipolar Planar Diodes: Dependences on Carrier Injection and Diode Area. IEEE Transactions on Electron Devices, 2017, 64, 2572-2578.	1.6	9

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19	Ni-Al-Ti Ohmic Contacts on Al Implanted 4H-SiC. Materials Science Forum, 2017, 897, 391-394.	0.3	8
20	Size effect on high temperature variable range hopping in Al⁺implanted 4H-SiC. Journal of Physics Condensed Matter, 2017, 29, 035703.	0.7	13
21	(Invited) Thermal Stability of 1Ã—1020cm-3Al+Implanted 4H-SiC after Electrical Activation at Temperature â‰¥ 1850Â°C. ECS Transactions, 2017, 80, 101-105.	0.3	1
22	Ni-Al-Ti Ohmic Contacts on 1 x 1020cm-3Al+Ion Implanted 4H-SiC. ECS Transactions, 2017, 80, 117-122.	0.3	1
23	(Invited) Thermal Stability of 1Ã—1020 cm-3 Al+ Implanted 4H-SiC after Electrical Activation at Temperature â‰¥ 1850Â°C. ECS Meeting Abstracts, 2017, , .	0.0	0
24	Ni-Al-Ti Ohmic Contacts on 1 x 1020 cm-3 Al+ Ion Implanted 4H-SiC. ECS Meeting Abstracts, 2017, , .	0.0	0
25	Al+ implanted vertical 4H-SiC p-i-n diodes: experimental and simulated forward current-voltage characteristics. MRS Advances, 2016, 1, 3637-3642.	0.5	2
26	1950Â°C Post Implantation Annealing of Al⁺Implanted 4H-SiC: Relevance of the Annealing Time. ECS Journal of Solid State Science and Technology, 2016, 5, P534-P539.	0.9	10
27	Structural and Functional Characterizations of Al⁺Implanted 4H-SiC Layers and Al⁺Implanted 4H-SiC<i>p-n</i>Junctions after 1950Â°C Post Implantation Annealing. ECS Journal of Solid State Science and Technology, 2016, 5, P621-P626.	0.9	19
28	Formation and Annihilation of Carbon Vacancies in 4H-SiC. Materials Science Forum, 2016, 858, 331-336.	0.3	2
29	1950Â°C Annealing of Al⁺ Implanted 4H-SiC: Sheet Resistance Dependence on the Annealing Time. Materials Science Forum, 2016, 858, 523-526.	0.3	1
30	(Invited) 4H-SiC Ion Implanted Bipolar Junctions: Relevance of the 1950ÂC Temperature for Post Implantation Annealing. ECS Transactions, 2016, 75, 171-181.	0.3	1
31	(Invited) 4H-SiC Ion Implanted Bipolar Junctions: Relevance of the 1950Â°C Temperature for Post Implantation Annealing. ECS Meeting Abstracts, 2016, , .	0.0	0
32	Elimination of carbon vacancies in 4H-SiC employing thermodynamic equilibrium conditions at moderate temperatures. Applied Physics Letters, 2015, 107, .	1.5	56
33	Remarks on the room temperature impurity band conduction in heavily Al+ implanted 4H-SiC. Journal of Applied Physics, 2015, 118, .	1.1	20
34	Voltage doubler rectifier based on 4H-SiC diodes for high-temperatures energy harvesting applications. , 2015, , .		2
35	Temperature sensor based on 4H-SiC diodes for hostile environments. , 2015, , .		0
36	Al⁺ Ion Implanted On-Axis <0001> Semi-Insulating 4H-SiC. Materials Science Forum, 2015, 821-823, 399-402.	0.3	0

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37	About the Hole Transport Analysis in Heavy Doped p-Type 4H-SiC(Al). Materials Science Forum, 2015, 821-823, 416-419.	0.3	0
38	Analytical Prediction of the Cross-Over Point in the Temperature Coefficient of the Forward Characteristics of 4Hâ˘SiC p⁺â˘iâ˘n Diodes. Materials Science Forum, 2015, 821-823, 628-631.	0.3	0
39	Hetero-Epitaxial Single Crystal 3C-SiC Opto-Mechanical Pressure Sensor. Materials Science Forum, 2015, 821-823, 902-905.	0.3	1
40	Formation of carbon vacancy in 4H silicon carbide during high-temperature processing. Journal of Applied Physics, 2014, 115, .	1.1	49
41	Temperature dependent current-voltage characteristics of microwave annealed Al⁺ implanted 4H-SiC p⁺-i-n diodes. , 2014, , .		1
42	On the Crossing-Point of 4H-SiC Power Diodes Characteristics. IEEE Electron Device Letters, 2014, 35, 244-246.	2.2	19
43	P+ implanted 6H-SiC n+-i-p diodes: evidence for a post-implantation-annealing dependent defect activation. Materials Research Society Symposia Proceedings, 2014, 1693, 131.	0.1	2
44	Microwave Annealing of High Dose Al+-implanted 4H-SiC: Towards Device Fabrication. Journal of Electronic Materials, 2014, 43, 843-849.	1.0	6
45	Analysis of the hole transport through valence band states in heavy Al doped 4H-SiC by ion implantation. Journal of Applied Physics, 2013, 114, .	1.1	48
46	Al⁺ Implanted Anode for 4H-SiC p-i-n Diodes. ECS Transactions, 2013, 50, 391-397.	0.3	14
47	Conventional thermal annealing for a more efficient p-type doping of Al⁺ implanted 4H-SiC. Journal of Materials Research, 2013, 28, 17-22.	1.2	41
48	Steady-State Analysis of a Normally-Off 4H-SiC Trench Bipolar-Mode FET. Materials Science Forum, 2013, 740-742, 942-945.	0.3	5
49	${m Al}^{+}$ Implanted 4H-SiC ${m p}^{+}$-i-n Diodes: Forward Current Negative Temperature Coefficient. IEEE Electron Device Letters, 2013, 34, 966-968.	2.2	21
50	Basal Plane Dislocation Mitigation Using High Temperature Annealing in 4H-SiC Epitaxy. ECS Transactions, 2013, 58, 325-329.	0.3	0
51	High Dose Al⁺ Implanted and Microwave Annealed 4H-SiC. Materials Science Forum, 2012, 717-720, 817-820.	0.3	0
52	Fully implanted vertical pâ€“iâ€“n diodes using high-purity semi-insulating 4Hâ€“SiC wafers. Semiconductor Science and Technology, 2012, 27, 055005.	1.0	4
53	High-Dose Phosphorus-Implanted 4H-SiC: Microwave and Conventional Post-Implantation Annealing at Temperatures â‰¥1700Â°C. Journal of Electronic Materials, 2012, 41, 457-465.	1.0	18
54	Microwave Annealing of Very High Dose Aluminum-Implanted 4H-SiC. Applied Physics Express, 2011, 4, 111301.	1.1	30

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55	Microwave Annealing of Ion Implanted 4H-SiC. , 2011, , .		0
56	Improving Doping Efficiency of P⁺ Implanted Ions in 4H-SiC. Materials Science Forum, 2011, 679-680, 393-396.	0.3	4
57	Non-Nitridated Oxides: Abnormal Behaviour of N-4H-SiC/SiO₂ Capacitors at Low Temperature Caused by near Interface States. Materials Science Forum, 2011, 679-680, 346-349.	0.3	4
58	Simulation of the Incomplete Ionization of the <i>n</i>-Type Dopant Phosphorus in 4H-SiC, Including Screening by Free Carriers. Materials Science Forum, 2011, 679-680, 397-400.	0.3	0
59	Passivation by N Implantation of the SiO2/SiC Acceptor Interface States: Impact on the Oxide Hole Traps and the Gate Oxide Reliability. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	0
60	Ultra Fast High Temperature Microwave Annealing of Ion Implanted Large Bandgap Semiconductors. Materials Science Forum, 2010, 645-648, 709-712.	0.3	0
61	Analysis of electron traps at the 4Hâ€“SiC/SiO2 interface; influence by nitrogen implantation prior to wet oxidation. Journal of Applied Physics, 2010, 108, 024503.	1.1	27
62	Effect of nitrogen implantation at the SiO2/SiC interface on the electron mobility and free carrier density in 4H-SiC metal oxide semiconductor field effect transistor channel. Journal of Applied Physics, 2010, 107, .	1.1	17
63	Carbon-Cap for Ohmic Contacts on Ion-Implanted 4Hâ€“SiC. Electrochemical and Solid-State Letters, 2010, 13, H432.	2.2	48
64	Analysis of the Electron Traps at the 4H-SiC/SiO₂ Interface of a Gate Oxide Obtained by Wet Oxidation of a Nitrogen Pre-Implanted Layer. Materials Science Forum, 2009, 615-617, 533-536.	0.3	0
65	C-V and DLTS Analyses of Trap-Induced Graded Junctions: The Case of Al⁺ Implanted JTE p⁺n 4H-SiC Diodes. Materials Science Forum, 2009, 615-617, 469-472.	0.3	0
66	Comparison between cathodoluminescence spectroscopy and capacitance transient spectroscopy on Al+ ion implanted 4H-SiC p+/n diodes. Superlattices and Microstructures, 2009, 45, 383-387.	1.4	12
67	Numerical simulations of Al implanted 4H-SiC diodes modeling an explicit carrier trap effect due to the non-substitutional Al doping concentration. , 2009, , .		2
68	Experimental characterization and numerical analysis of the 4H-SiC pâ€“iâ€“n diodes static and transient behaviour. Microelectronics Journal, 2008, 39, 1594-1599.	1.1	23
69	Nitrogen Implantation to Improve Electron Channel Mobility in 4H-SiC MOSFET. IEEE Transactions on Electron Devices, 2008, 55, 961-967.	1.6	41
70	Investigation on the Use of Nitrogen Implantation to Improve the Performance of N-Channel Enhancement 4H-SiC MOSFETs. IEEE Transactions on Electron Devices, 2008, 55, 2021-2028.	1.6	20
71	Effects of Very High Neutron Fluence Irradiation on p⁺n Junction 4H-SiC Diodes. Materials Science Forum, 2007, 556-557, 917-920.	0.3	9
72	Electrical properties of Al2O3â^•4Hâ€SiC structures grown by atomic layer chemical vapor deposition. Journal of Applied Physics, 2007, 102, 054513.	1.1	41

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73	Fabrication of MOS Capacitors by Wet Oxidation of p-Type 4H-SiC Preamorphized by Nitrogen Ion Implantation. Materials Science Forum, 2007, 556-557, 651-654.	0.3	3
74	Characterization of MOS Capacitors Fabricated on n-type 4H-SiC Implanted with Nitrogen at High Dose. Materials Science Forum, 2007, 556-557, 639-642.	0.3	4
75	Post-Implantation Annealing of SiC: Relevance of the Heating Rate. Materials Science Forum, 2007, 556-557, 561-566.	0.3	2
76	X-Ray and AFM Analysis of Al₂O₃ Deposited by ALCVD on n-Type 4H-SiC. Materials Science Forum, 2007, 556-557, 683-686.	0.3	4
77	Analysis of the Electrical Activation of P⁺ Implanted Layers as a Function of the Heating Rate of the Annealing Process. Materials Science Forum, 2007, 556-557, 571-574.	0.3	2
78	Characterization of energy levels related to impurities in epitaxial 4H-SiC ion implanted p+n junctions. Diamond and Related Materials, 2007, 16, 6-11.	1.8	9
79	Annealing effects on leakage current and epilayer doping concentration of p+n junction 4H-SiC diodes after very high neutron irradiation. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2007, 583, 173-176.	0.7	9
80	MOS capacitors obtained by wet oxidation of n-type 4Hâ€“SiC pre-implanted with nitrogen. Microelectronic Engineering, 2007, 84, 2804-2809.	1.1	21
81	Simulation and experimental results on the forward Jâ€“V characteristic of Al implanted 4Hâ€“SiC pâ€“iâ€“n diodes. Microelectronics Journal, 2007, 38, 1273-1279.	1.1	25
82	Silane overpressure post-implant annealing of Al dopants in SiC: Cold wall CVD apparatus. Applied Surface Science, 2006, 252, 3837-3842.	3.1	6
83	Current Analysis of Ion Implanted p⁺/n 4H-SiC Junctions: Post-Implantation Annealing in Ar Ambient. Materials Science Forum, 2006, 527-529, 815-818.	0.3	7
84	Ion Implanted p+/n 4H-SiC Junctions: effect of the Heating Rate during Post Implantation Annealing. Materials Research Society Symposia Proceedings, 2006, 911, 1.	0.1	4
85	Minimum Ionizing Particle Detector Based on p⁺n Junction SiC Diode. Materials Science Forum, 2006, 527-529, 1469-1472.	0.3	1
86	Ion Implanted p⁺/n Diodes: Post-Implantation Annealing in a Silane Ambient in a Cold-Wall Low-Pressure CVD Reactor. Materials Science Forum, 2006, 527-529, 819-822.	0.3	0
87	Interfacial Properties of SiO₂ Grown on 4H-SiC: Comparison between N₂O and Wet O₂ Oxidation Ambient. Materials Science Forum, 2006, 527-529, 979-982.	0.3	6
88	Post-Implantation Annealing in a Silane Ambient Using Hot-Wall CVD. Materials Science Forum, 2006, 527-529, 839-842.	0.3	1
89	Correlation between Current Transport and Defects in n⁺/p 6H-SiC Diodes. Materials Science Forum, 2006, 527-529, 811-814.	0.3	2
90	Radiation hardness after very high neutron irradiation of minimum ionizing particle detectors based on 4H-SiC p/sup +/n junctions. IEEE Transactions on Nuclear Science, 2006, 53, 1557-1563.	1.2	59

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91	Effects of heating ramp rates on the characteristics of Al implanted 4Hâ€“SiC junctions. Applied Physics Letters, 2006, 88, 162106.	1.5	27
92	Measurements and simulations of charge collection efficiency of p+/n junction SiC detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2005, 546, 218-221.	0.7	16
93	Measurements of Charge Collection Efficiency of p⁺/n Junction SiC Detectors. Materials Science Forum, 2005, 483-485, 1021-1024.	0.3	9
94	Ar Annealing at 1600Â°C and 1650Â°C of Al⁺ Implanted p⁺/n 4H-SiC Diodes: Analysis of the J-V Characteristics Versus Annealing Temperature. Materials Science Forum, 2005, 483-485, 625-628.	0.3	2
95	n⁺/p Diodes Realized in SiC by Phosphorus Ion Implantation: Electrical Characterization as a Function of Temperature. Materials Science Forum, 2005, 483-485, 649-652.	0.3	1
96	Ni-Silicide Contacts to 6H-SiC: Contact Resistivity and Barrier Height on Ion Implanted n-Type and Barrier Height on p-Type Epilayer. Materials Science Forum, 2005, 483-485, 737-740.	0.3	3
97	Competition between Oxidation and Recrystallization in Ion Amorphized (0001) 6H-SiC. Materials Science Forum, 2005, 483-485, 665-668.	0.3	0
98	J-V Characteristics of Al⁺ Ion Implanted p⁺/n 4H-SiC Diodes Annealed in Silane Ambient at 1600Â°C. Materials Science Forum, 2005, 483-485, 629-632.	0.3	1
99	Oxidation kinetics of ion-amorphized (0001) 6Hâ€“SiC: Competition between oxidation and recrystallization processes. Applied Physics Letters, 2005, 86, 121907.	1.5	12
100	The Role of the Ion Implanted Emitter State on 6H-SiC Power Diodes Behavior. A Statistical Study. Materials Science Forum, 2004, 457-460, 1025-1028.	0.3	2
101	SiC Donor Doping by 300Â°C P Implantation: Characterization of the Doped Layer Properties in Dependence of the Post-Implantation Annealing Temperature. Materials Science Forum, 2004, 457-460, 945-950.	0.3	5
102	Contact Resistivity and Barrier Height of Al/Ti Ohmic Contacts on p-Type Ion Implanted 4H- and 6H-SiC. Materials Science Forum, 2004, 457-460, 881-884.	0.3	15
103	Characterization of a Thermal Oxidation Process on SiC Preamorphized by Ar Ion Implantation. Materials Science Forum, 2004, 457-460, 1357-1360.	0.3	1
104	A Robust Process for Ion Implant Annealing of SiC in a Low-Pressure Silane Ambient. Materials Research Society Symposia Proceedings, 2004, 815, 1.	0.1	8
105	A Highly Effective Edge Termination Design for SiC Planar High Power Devices. Materials Science Forum, 2004, 457-460, 1253-1256.	0.3	9
106	Extraction of the Schottky Barrier Height for Ti/Al Contacts on 4H-SiC from I-V and C-V Measurements. Materials Science Forum, 2004, 457-460, 993-996.	0.3	4
107	Structural Characterization of Alloyed Al/Ti and Ti Contacts on SiC. Materials Science Forum, 2004, 457-460, 837-840.	0.3	10
108	Low temperature oxidation of SiC preamorphized by ion implantation. Journal of Applied Physics, 2004, 95, 6119-6123.	1.1	15

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109	Al/Ti Ohmic Contacts to p-Type Ion-Implanted 6H-SiC: Mono- and Two- Dimensional Analysis of TLM Data. Materials Science Forum, 2003, 433-436, 673-676.	0.3	7
110	Electrical Characterization of Ion-Implanted n⁺/p 6H-SiC Diodes. Materials Science Forum, 2003, 433-436, 621-624.	0.3	0
111	He+ ion damage in 4H-SiC studied by charge collection efficiency measurements.. Materials Research Society Symposia Proceedings, 2003, 792, 407.	0.1	0
112	Improved electrical characterization of Alâ€“Ti ohmic contacts on p-type ion implanted 6H-SiC. Semiconductor Science and Technology, 2003, 18, 554-559.	1.0	25
113	Comparison between Chemical and Electrical Profiles in Al⁺ or N⁺ Implanted and Annealed 6H-SiC. Materials Science Forum, 2002, 389-393, 811-814.	0.3	1
114	Low-Temperature Thermal Oxidation of Ion-Amorphized 6H-SiC. Materials Science Forum, 2002, 389-393, 1109-1112.	0.3	8
115	A Comparative Study of High-Temperature Aluminum Post-Implantation Annealing in 6H- and 4H-SiC, Non-Uniform Temperature Effects. Materials Science Forum, 2002, 389-393, 827-830.	0.3	13
116	Highly-Doped Implanted pn Junction for SiC Zener Diode Fabrication. Materials Science Forum, 2002, 389-393, 1317-1320.	0.3	3
117	<0001> channeling stopping power of MeV He+ ions in 4H- and 6H-SiC.. Materials Research Society Symposia Proceedings, 2002, 742, 2121.	0.1	1
118	Contact resistivity of Al/Ti ohmic contacts on p-type ion implanted 4H- and 6H-SiC.. Materials Research Society Symposia Proceedings, 2002, 742, 621.	0.1	13
119	Charge states distribution of 0.16â€“3.3 MeV He ions transmitted through silicon. Nuclear Instruments & Methods in Physics Research B, 2002, 193, 66-70.	0.6	10
120	Charged Particle Detection Properties of Epitaxial 4H-SiC Schottky Diodes. Materials Science Forum, 2001, 353-356, 757-762.	0.3	21
121	The Monte Carlo Binary Collision Approximation Applied to the Simulation of the Ion Implantation Process in Single Crystal SiC: High Dose Effects. Materials Science Forum, 2001, 353-356, 599-602.	0.3	5
122	4H- and 6H-SiC Rutherford Back Scattering-Channeling Spectrometry: Polytype Finger Printing. Materials Science Forum, 2001, 353-356, 279-282.	0.3	2
123	Structural characterization of Ar⁺-ion-amorphized 6H-SiC wafers annealed at 1100 Â°C in N₂ or wet O₂ ambient. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 2000, 80, 647-659.	0.6	10
124	Structural, optical and chemical characterization of 300Â°C, MeV ion implanted and 1700Â°C annealed 6H-SiC. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	0
125	The Si surface yield as a calibration standard for RBS. Nuclear Instruments & Methods in Physics Research B, 2000, 161-163, 293-296.	0.6	28
126	Determination of He electronic energy loss in crystalline Si by Monte-Carlo simulation of Rutherford backscatteringâ€“channeling spectra. Nuclear Instruments & Methods in Physics Research B, 2000, 170, 1-9.	0.6	49

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127	Structural characterization of Ar + -ion-amorphized 6H-SiC wafers annealed at 1100 o C in N 2 or wet O 2 ambient. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 2000, 80, 647-659.	0.6	2
128	A study about the wet oxidation of crystalline and ion damaged 6H-SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 475-479.	1.7	12
129	Binary collision approximation modeling of ion-induced damage effects in crystalline 6Hâ€“SiC. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 573-577.	0.6	14
130	A study of He+ ion-induced damage in silicon by quantitative analysis of charge collection efficiency data. Nuclear Instruments & Methods in Physics Research B, 1998, 136-138, 1340-1344.	0.6	8
131	RBS-channeling analysis of virgin 6Hî—,SiC: Experiments and Monte Carlo simulations. Nuclear Instruments & Methods in Physics Research B, 1998, 136-138, 1267-1271.	0.6	7
132	Stopping and damage parameters for Monte Carlo simulation of MeV implants in crystalline Si. Journal of Applied Physics, 1997, 82, 5958-5964.	1.1	37
133	Simulation of pulse height spectra in ion beam induced charge microscopy of polycrystalline silicon. Journal of Applied Physics, 1997, 82, 742-747.	1.1	15
134	Ion implantation induced swelling in 6H-SiC. Applied Physics Letters, 1997, 70, 3425-3427.	1.5	62
135	Chapter 8 Rutherford Backscattering Studies of Ion Implanted Semiconductors. Semiconductors and Semimetals, 1997, , 239-260.	0.4	2
136	MeV ion implantation induced damage in relaxed Si1â^'xGex. Journal of Applied Physics, 1997, 81, 2208-2218.	1.1	14
137	RBS-channeling determination of damage profiles in fully relaxed Si0.76Ge0.24 implanted with 2 MeV Si ions. Nuclear Instruments & Methods in Physics Research B, 1997, 122, 689-695.	0.6	10
138	The Legnaro ion microprobe in low current experiments. Nuclear Instruments & Methods in Physics Research B, 1997, 130, 25-30.	0.6	5
139	Ion implantation induced damage in relaxed Si0.75Ge0.25. Nuclear Instruments & Methods in Physics Research B, 1996, 112, 301-304.	0.6	5
140	Damage profiles in as-implanted silicon: fluence dependence. Nuclear Instruments & Methods in Physics Research B, 1996, 112, 148-151.	0.6	5
141	Dynamic Monte Carlo simulation of nonlinear damage growth during ion implantation of crystalline silicon. Nuclear Instruments & Methods in Physics Research B, 1996, 112, 152-155.	0.6	12
142	Different methods for the determination of damage profiles in Si from RBS-channeling spectra: a comparison. Nuclear Instruments & Methods in Physics Research B, 1996, 118, 128-132.	0.6	57
143	Damage profiles in as-implanted â€ˆ100â€‰ Si crystals: strain by X-ray diffractometry versus interstitials by RBS-channeling. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 64-67.	0.6	3
144	Images of grain boundaries in polycrystalline silicon solar cells by electron and ion beam induced charge collection. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 306-310.	1.7	12

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145	Dynamic Monte Carlo simulation of nonlinear damage growth during ion implantation of crystalline silicon. , 1996, , 152-155.		0
146	Damage profiles in as-implanted silicon: fluence dependence. , 1996, , 148-151.		0
147	Ion implantation induced damage in relaxed Si0.75Ge0.25. , 1996, , 301-304.		0
148	EPR and X-ray diffraction study of damage produced by implantation of B ions (50 keV, 1 MeV) or Si ions (50 keV, 700 keV, 1.5 MeV) into silicon. Nuclear Instruments & Methods in Physics Research B, 1995, 96, 215-218.	0.6	19
149	RBS-channeling spectra: simulation of as-implanted Si samples through an empirical formula for â€ˆ100â€‰ axial dechanneling of He in silicon. Nuclear Instruments & Methods in Physics Research B, 1994, 84, 507-511.	0.6	15
150	Energy loss and equilibrium charge distribution of nitrogen ions transmitted through thin silicon crystals. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 33-36.	0.6	9
151	X-ray diffraction analysis of damage accumulation due to the nuclear energy loss of 50 keV and 1â€“2.2 MeV B ions implanted in silicon. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 624-627.	0.6	14
152	Structural and electrical characterization of YBa2Cu3O7â˜'x thin films grown on different substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1992, 14, 422-425.	1.7	3
153	X-ray determination of lattice damage depth-profiles due to electronic and nuclear energy losses in silicon implanted with MeV boron ions. Nuclear Instruments & Methods in Physics Research B, 1992, 66, 511-514.	0.6	9
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